ABSOLUTE MAXIMUM RATINGS

Gate-Drain, Gate-Source Voltage . . . . . –25 V
Gate Current . . . . . 10 mA
Lead Temperature . . . . . 300°C
Storage Temperature . . . . . –65 to 150°C
Operating Junction Temperature . . . . . –55 to 150°C
Power Dissipation[a] . . . . . 350 mW

Notes
a. Derate 2.8 mW/°C above 25°C

SPECIFICATIONS FOR 2N SERIES (T_A = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions		Typ[a]	Limits 2N5484 Min	2N5484 Max	2N5485 Min	2N5485 Max	2N5486 Min	2N5486 Max	Unit
Static											
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	I_G = –1 μA , V_{DS} = 0 V		–35	–25		–25		–25		V
Gate-Source Cutoff Voltage	$V_{GS(off)}$	V_{DS} = 15 V, I_D = 10 nA			–0.3	–3	–0.5	–4	–2	–6	
Saturation Drain Current[b]	I_{DSS}	V_{DS} = 15 V, V_{GS} = 0 V			1	5	4	10	8	20	mA
Gate Reverse Current	I_{GSS}	V_{GS} = –20 V, V_{DS} = 0 V		–0.002		–1		–1		–1	nA
			T_A = 100°C	–0.2		–200		–200		–200	
Gate Operating Current[c]	I_G	V_{DG} = 10 V, I_D = 1 mA		–20							pA
Gate-Source Forward Voltage[c]	$V_{GS(F)}$	I_G = 10 mA , V_{DS} = 0 V		0.8							V
Dynamic											
Common-Source Forward Transconductance[NO TAG]	g_{fs}	V_{DS} = 15 V, V_{GS} = 0 V f = 1 kHz			3	6	3.5	7	4	8	mS
Common-Source Output Conductance[NO TAG]	g_{os}					50		60		75	μS
Common-Source Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V f = 1 MHz		2.2		5		5		5	pF
Common-Source Reverse Transfer Capacitance	C_{rss}			0.7		1		1		1	
Common-Source Output Capacitance	C_{oss}			1		2		2		2	
Equivalent Input Noise Voltage[c]	$\overline{e}_n$	V_{DS} = 15 V, V_{GS} = 0 V f = 100 Hz		10							nV/√Hz
High-Frequency											
Common-Source Transconductance[d]	$Y_{fs(RE)}$	V_{DS} = 15 V V_{GS} = 0 V	f = 100 MHz	5.5	2.5						mS
			f = 400 MHz	5.5			3		3.5		
Common-Source Output Conductance[d]	$Y_{os(RE)}$		f = 100 MHz	45		75					μS
			f = 400 MHz	65				100		100	
Common-Source Input Conductance[d]	$Y_{is(RE)}$		f = 100 MHz	0.05		0.1					mS
			f = 400 MHz	0.8				1		1	
Common-Source Power Gain[d]	G_{ps}	V_{DS} = 15 V, I_D = 1 mA f = 100 MHz		20	16	25					dB
		V_{DS} = 15 V I_D = 4 mA	f = 100 MHz	21			18	30	18	30	
			f = 400 MHz	13			10	20	10	20	
Noise Figure[d]	NF	V_{DS} = 15 V, V_{GS} = 0 V R_G = 1 MΩ, f = 1 kHz		0.3		2.5		2.5		2.5	
		V_{DS} = 15 V, I_D = 1 mA R_G = 1 kΩ, f = 100 MHz		2		3					
		V_{DS} = 15 V I_D = 4 mA R_G = 1 kΩ	f = 100 MHz	1				2		2	
			f = 400 MHz	2.5				4		4	

SPECIFICATIONS FOR SST SERIES (T_A = 25°C UNLESS OTHERWISE NOTED)

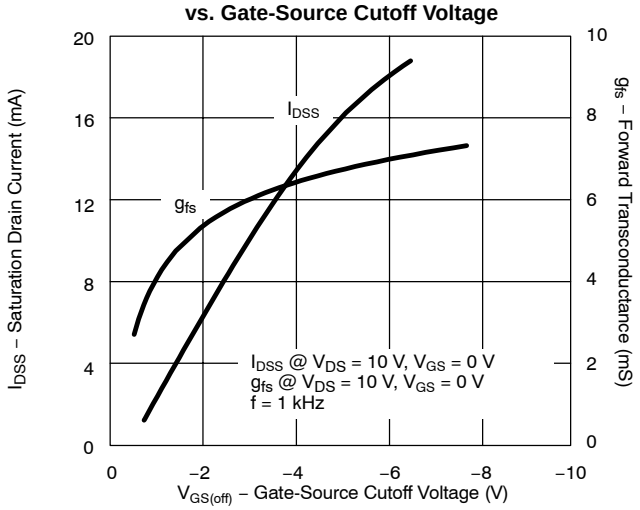
Parameter	Symbol	Test Conditions	Typ[b]	Limits SST5484 Min	SST5484 Max	SST5485 Min	SST5485 Max	SST5486 Min	SST5486 Max	Unit
Static										
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	I_G = −1 μA , V_{DS} = 0 V	−35	−25		−25		−25		V
Gate-Source Cutoff Voltage	$V_{GS(off)}$	V_{DS} = 15 V, I_D = 10 nA		−0.3	−3	−0.5	−4	−2	−6	
Saturation Drain Current[b]	I_{DSS}	V_{DS} = 15 V, V_{GS} = 0 V		1	5	4	10	8	20	mA
Gate Reverse Current	I_{GSS}	V_{GS} = −20 V, V_{DS} = 0 V	−0.002		−1		−1		−1	nA
		T_A = 100°C	−0.2		−200		−200		−200	
Gate Operating Current[c]	I_G	V_{DG} = 10 V, I_D = 1 mA	−20							pA
Gate-Source Forward Voltage[c]	$V_{GS(F)}$	I_G = 10 mA , V_{DS} = 0 V	0.8							V
Dynamic										
Common-Source Forward Transconductance[NO TAG]	g_{fs}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 kHz		3	6	3.5	7	4	8	mS
Common-Source Output Conductance[NO TAG]	g_{os}				50		60		75	μS
Common-Source Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz	2.2							pF
Common-Source Reverse Transfer Capacitance	C_{rss}		0.7							
Common-Source Output Capacitance	C_{oss}		1							
Equivalent Input Noise Voltage[c]	$\overline{e}_n$	V_{DS} = 15 V, V_{GS} = 0 V, f = 100 Hz	10							$\frac{nV}{\sqrt{Hz}}$
High-Frequency										
Common-Source Transconductance	Y_{fs}	V_{DS} = 15 V, V_{GS} = 0 V, f = 100 MHz	5.5							mS
		f = 400 MHz	5.5							
Common-Source Output Conductance	Y_{os}	f = 100 MHz	45							μS
		f = 400 MHz	65							
Common-Source Input Conductance	Y_{is}	f = 100 MHz	0.05							mS
		f = 400 MHz	0.8							
Common-Source Power Gain	G_{ps}	V_{DS} = 15 V, I_D = 1 mA, f = 100 MHz	20							dB
		V_{DS} = 15 V, I_D = 4 mA, f = 100 MHz	21							
		f = 400 MHz	13							
Noise Figure	NF	V_{DS} = 15 V, V_{GS} = 0 V, R_G = 1 MΩ, f = 1 kHz	0.3							
		V_{DS} = 15 V, I_D = 1 mA, R_G = 1 kΩ, f = 100 MHz	2							
		V_{DS} = 15 V, I_D = 4 mA, R_G = 1 kΩ, f = 100 MHz	1							
		f = 400 MHz	2.5							

Notes
a. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing. NH
b. Pulse test: PW ≤300 μs duty cycle ≤3%.
c. This parameter not registered with JEDEC.
d. Not a production test.

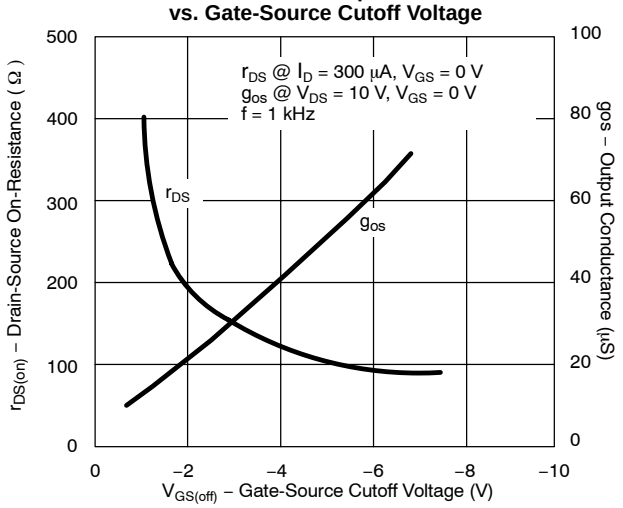
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)

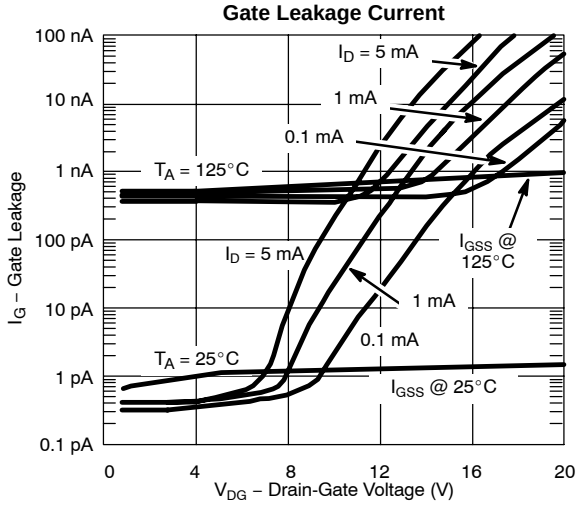
Drain Current and Transconductance vs. Gate-Source Cutoff Voltage



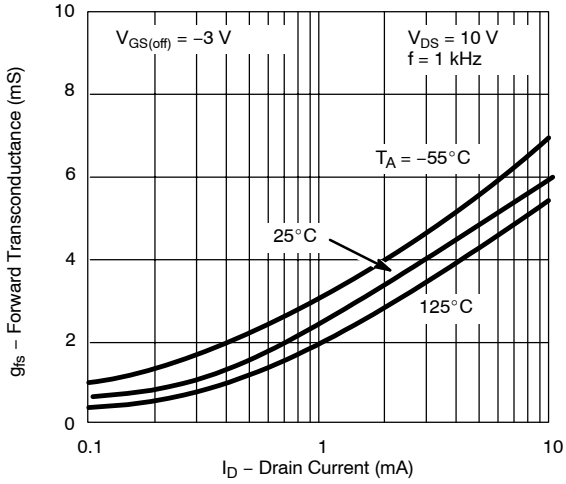
On-Resistance and Output Conductance vs. Gate-Source Cutoff Voltage



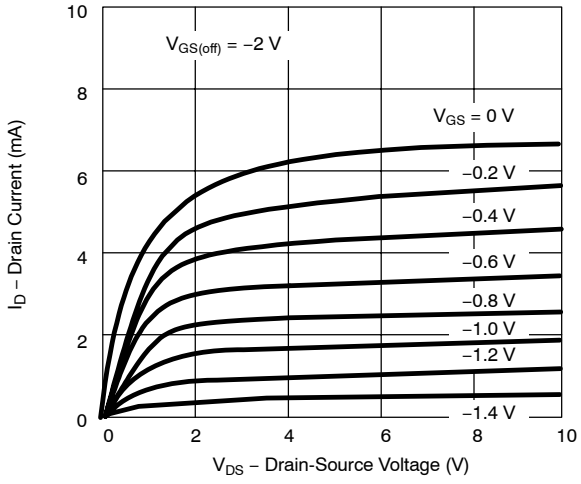
Gate Leakage Current



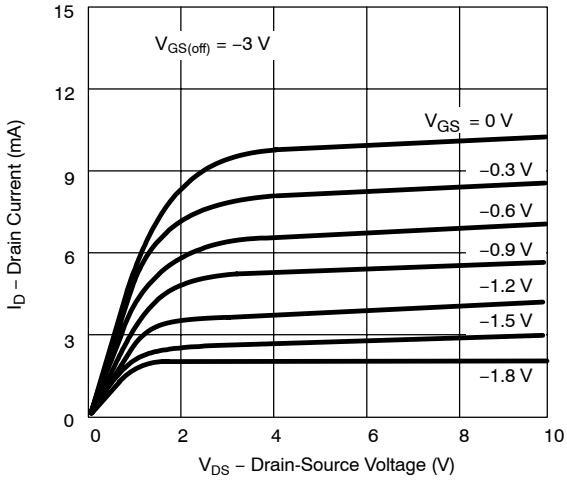
Common-Source Forward Transconductance vs. Drain Current



Output Characteristics

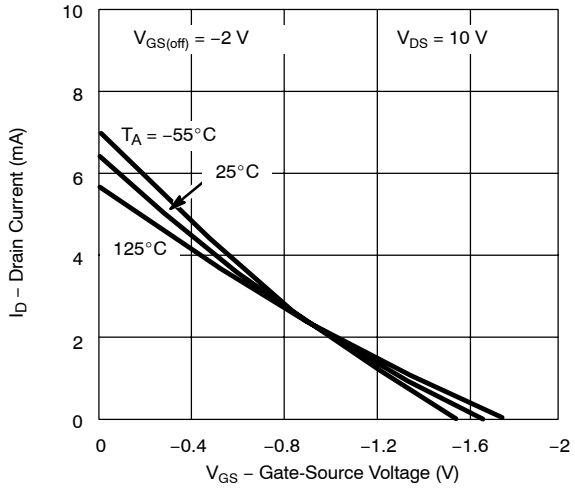


Output Characteristics

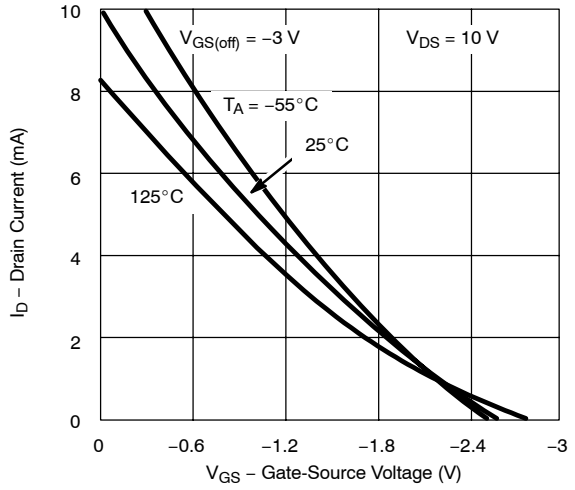


TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)

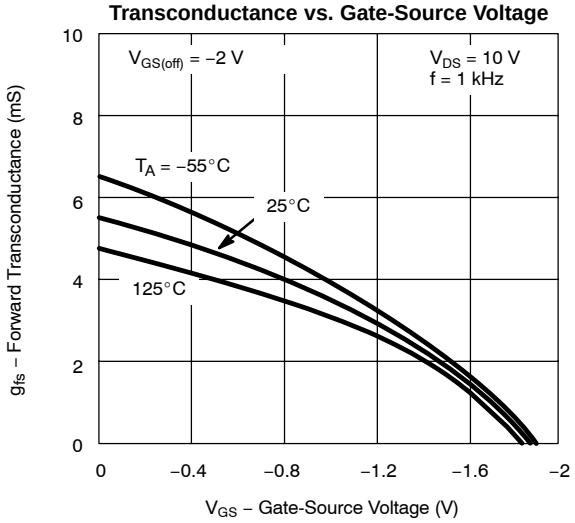
Transfer Characteristics



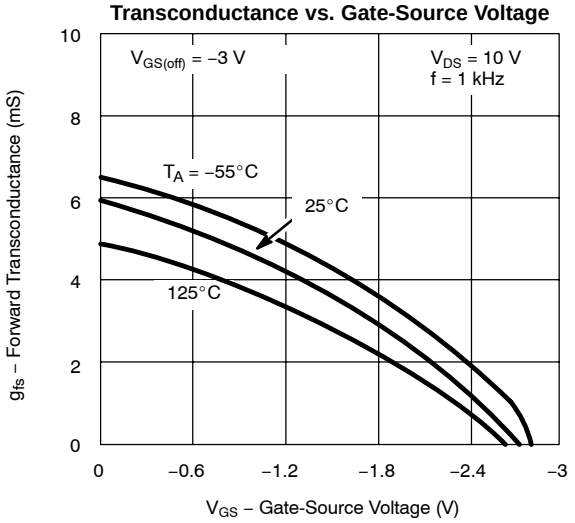
Transfer Characteristics



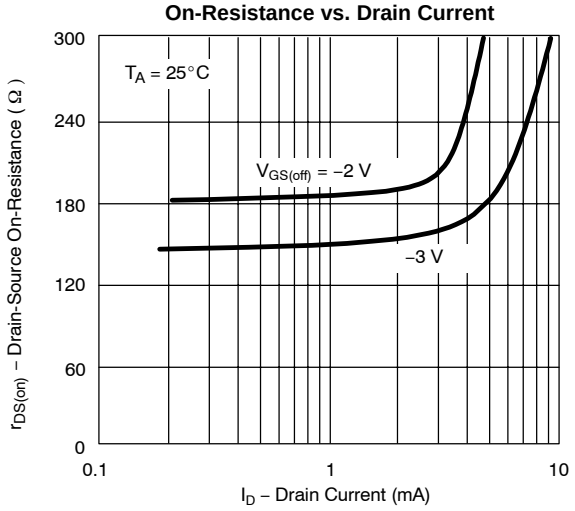
Transconductance vs. Gate-Source Voltage



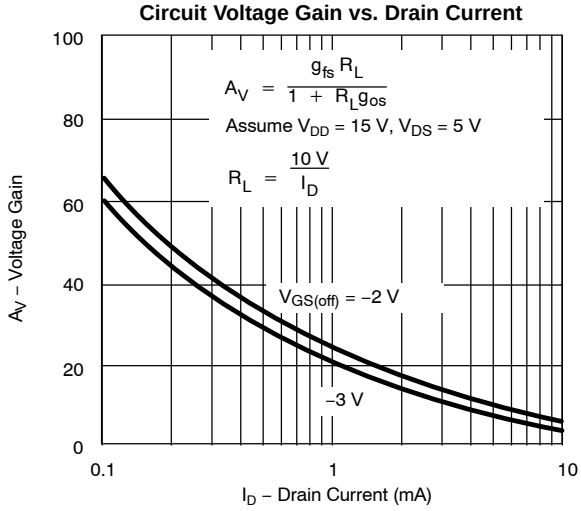
Transconductance vs. Gate-Source Voltage



On-Resistance vs. Drain Current

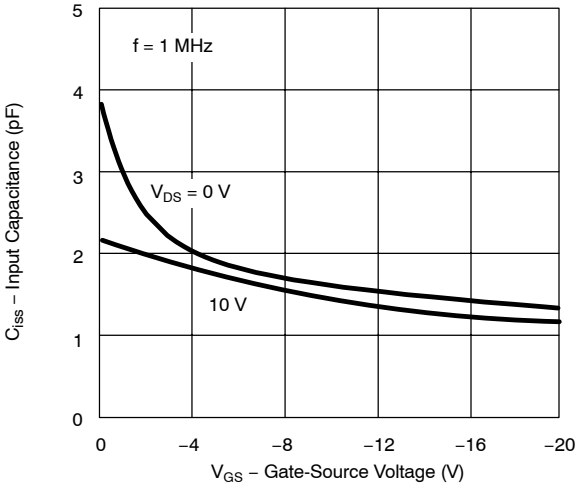


Circuit Voltage Gain vs. Drain Current

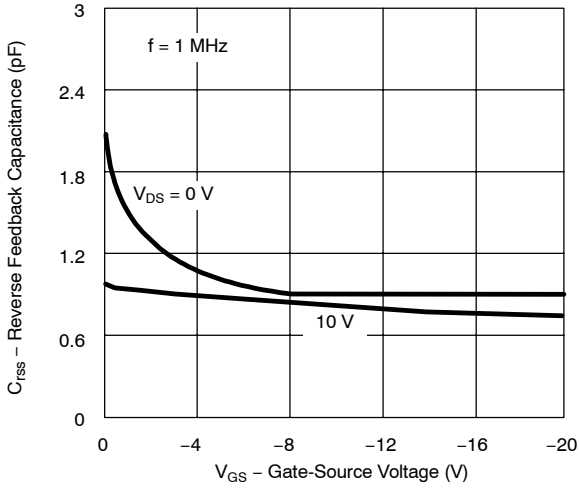


TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)

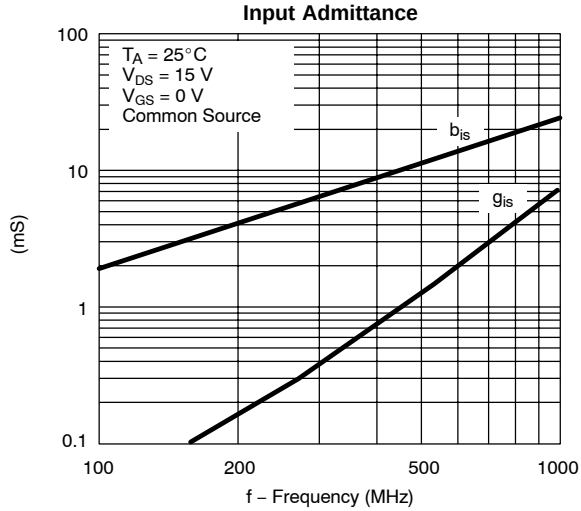
Common-Source Input Capacitance vs. Gate-Source Voltage



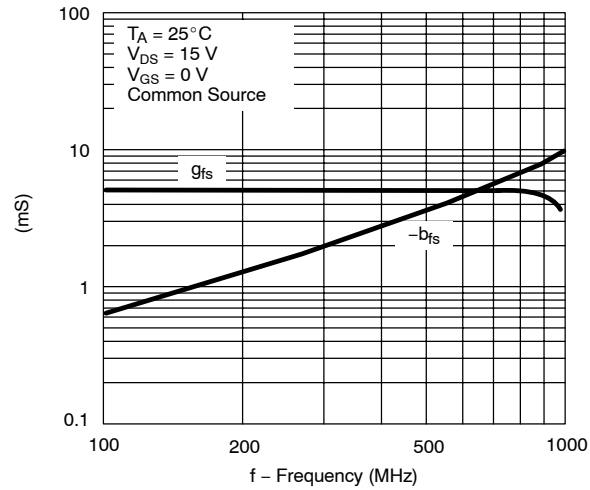
Common-Source Reverse Feedback Capacitance vs. Gate-Source Voltage



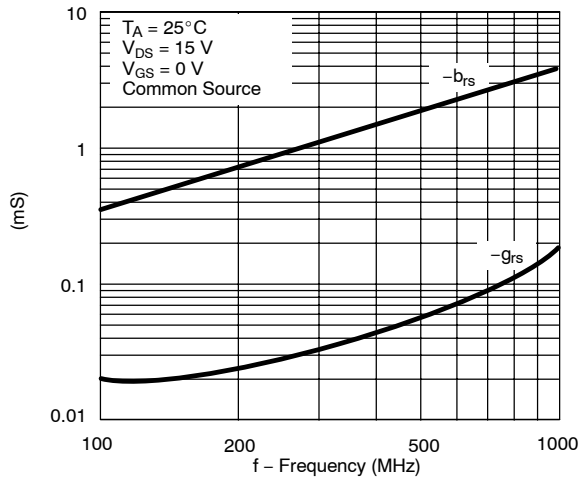
Input Admittance



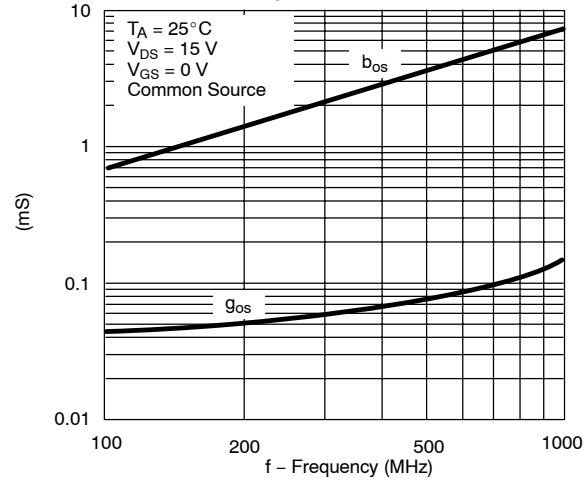
Forward Admittance



Reverse Admittance

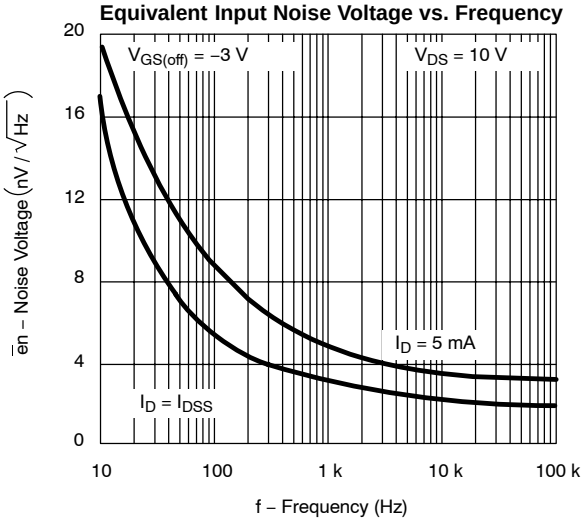


Output Admittance

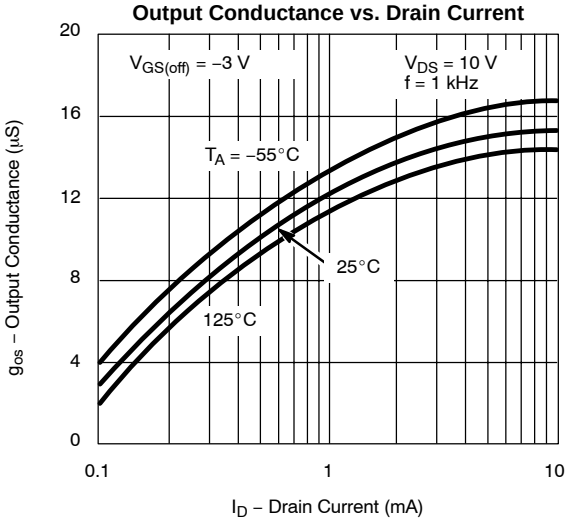


TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)

Equivalent Input Noise Voltage vs. Frequency



Output Conductance vs. Drain Current



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?70246.

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.